

A1+ Claim 4 (amended). The method of Claim 19 comprising applying a silane adhesion promoter material to the first surface of the wafer before applying the protective material to the wafer.

Claim 6 (amended). The method of Claim 19 wherein slot forming step is conducted using a grit blast material selected from alumina and silicon carbide.

A2 Claim 7 (amended). The method of Claim 19 wherein the first layer comprises a silane adhesion promoter layer and a photoresist layer and the protective layer comprises a polyacrylamide layer, further comprising substantially removing the polyacrylamide layer subsequent to the slot forming step to provide a wafer containing the silane layer and the photoresist layer.

A3 Claim 13 (amended). The method of Claim 20 wherein the grit blasting step is conducted using a grit blast material selected from alumina and silicon carbide.

Claim 14 (amended). The method of Claim 20 wherein the first layer comprises a photoresist layer and the second layer comprises a polyacrylamide layer applied to the photoresist layer.

A4 Claim 17 (amended). The method of Claim 20 wherein the first layer comprises a photoresist material having a thickness ranging from about 1 to about 10 microns.

Please add the following new claims 19 and 20.

A5 Claim 19 (new) In a method for forming one or more slots in a silicon wafer containing a first surface and a second surface opposite the first surface, the improvement comprising the steps of:

forming a substantially permanent non-water soluble first layer on the first surface of the wafer from a material selected from the group consisting of silane materials, photoresist materials, and a combination of silane and photoresist materials;

applying a water-soluble protective material to the first layer to form a protective second layer thereon;

forming one or more slots in the silicon wafer extending through the wafer from the first surface to the second surface thereof; and

removing the water-soluble second layer from the wafer.

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Claim 20 (new) In a method for making ink jet printheads from a silicon wafer having a device surface side and one or more ink feed vias grit blasted therein for ink feed to the device surface side thereof, the ink jet printheads including nozzle plates attached to the device surface side of the wafer, providing nozzle plate/chip assemblies, and TAB circuits or flexible circuits electrically connected to the nozzle plate/chip assemblies, the improvement comprising:

spin coating a substantially water-insoluble first material on a the device surface side of a silicon wafer to form a first layer thereon, the first material being selected from the group consisting of a silane material, a photoresist material, and a combination of silane material and photoresist material;

spin coating onto the first layer a substantially water-soluble protective material to provide a second layer on the first surface of the wafer;

grit blasting one or more ink vias in the wafer extending from a second surface thereof to the device surface side of the wafer; and

removing substantially all of the second layer from the wafer.
